



STP8NM60FP Information



For Reference Only

Part Number STP8NM60FP
Manufacturer STMicroelectronics

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 650V 8A TO-220FP

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









STP8NM60FP Specifications

Manufacturer Part Number STP8NM60FP Manufacturer STMicroelectronics Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series MDmesh? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 18nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ± 30V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack Report errors? Report errors?		
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Package TO-220-3 Full Pack Series MDmesh? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 650V Current - Continuous Drain (Id) @ 25°C 8A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 18nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Manufacturer	STMicroelectronics
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SeriesMDmesh?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250µAGate Charge (Qg) (Max) @ Vgs18nC @ 10VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs1 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs18nC @ 10VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs1 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Package	TO-220-3 Full Pack
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs18nC @ 10VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs1 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Series	MDmesh?
Drain to Source Voltage (Vdss)650 VCurrent - Continuous Drain (Id) @ 25°C8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs18nC @ 10VInput Capacitance (Ciss) (Max) @ Vds400pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs1 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Ba (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 18nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id St @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Drain to Source Voltage (Vdss)	650V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 5V @ 250μA 18nC @ 10V 18nC @ 10V 400pF @ 25V 25V 230V 10hm @ 2.5A, 10V 10hm @ 2.5A, 1	Current - Continuous Drain (Id) @ 25°C	8A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 400pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)30W (Tc)Rds On (Max) @ Id, Vgs1 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	18nC @ 10V
FET Feature - Power Dissipation (Max) 30W (Tc) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	400pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 1 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs1 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	30W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	1 Ohm @ 2.5A, 10V
Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220FP
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

STP8NM60FP Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

STP8NM60FP Payment Methods



















STP8NM60FP Shipping Methods













If you have any question about STP8NM60FP, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com